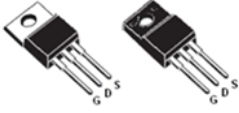
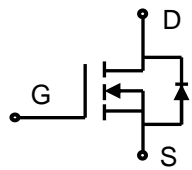



Lonten N-channel 650V, 7A Power MOSFET

<p>Description The Power MOSFET is fabricated using the advanced planar VDMOS technology. The resulting device has low conduction resistance, superior switching performance and high avalanche energy.</p> <p>Features</p> <ul style="list-style-type: none"> ◆ Low $R_{DS(on)}$ ◆ Low gate charge (typ. $Q_g = 20.7nC$) ◆ 100% UIS tested ◆ RoHS compliant <p>Applications</p> <ul style="list-style-type: none"> ◆ Power factor correction. ◆ Switched mode power supplies. ◆ LED driver. 	<p>Product Summary</p> <p>V_{DSS} 650V</p> <p>I_D 7A</p> <p>$R_{DS(on),max}$ 1.4Ω</p> <p>$Q_{g,typ}$ 20.7nC</p> <div style="text-align: center;">  <p>TO-220 TO-220F</p>  <p>N-Channel MOSFET</p> </div> <div style="text-align: right;">  </div>
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Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	650	V
Continuous drain current ($T_C = 25^\circ C$)	I_D	7	A
($T_C = 100^\circ C$)		4.3	A
Pulsed drain current ¹⁾	I_{DM}	28	A
Gate-Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse ²⁾	E_{AS}	352	mJ
Peak diode recovery dv/dt ³⁾	dv/dt	5	V/ns
Power Dissipation TO-220F ($T_C = 25^\circ C$)	P_D	39	W
Derate above 25°C		0.31	W/°C
Power Dissipation TO-220 ($T_C = 25^\circ C$)	P_D	100	W
Derate above 25°C		0.8	W/°C
Operating junction and storage temperature range	T_J, T_{STG}	-55 to +150	°C
Continuous diode forward current	I_S	7	A
Diode pulse current	$I_{S,pulse}$	28	A

Thermal Characteristics

Parameter	Symbol	Value		Unit
		TO-220F	TO-220	
Thermal resistance, Junction-to-case	$R_{\theta JC}$	3.2	1.25	°C/W
Thermal resistance, Junction-to-ambient	$R_{\theta JA}$	62.5	110	°C/W

Package Marking and Ordering Information

Device	Device Package	Marking	Units/Tube	Units/Real
LNC7N65	TO-220	LNC7N65	50	
LND7N65	TO-220F	LND7N65	50	

Electrical Characteristics
 $T_c = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DS}	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$	2	-	4	V
Drain cut-off current	I_{DSS}	$V_{DS}=650\text{ V}, V_{GS}=0\text{ V},$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	-	-	1	μA
Gate leakage current, Forward	I_{GSSF}	$V_{GS}=30\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
Gate leakage current, Reverse	I_{GSSR}	$V_{GS}=-30\text{ V}, V_{DS}=0\text{ V}$	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=3.5\text{ A}$	-	1.2	1.4	Ω
Dynamic characteristics						
Input capacitance	C_{iss}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$	-	1090	-	pF
Output capacitance	C_{oss}		-	111	-	
Reverse transfer capacitance	C_{rss}		-	6.1	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 325\text{ V}, I_D = 7\text{ A}$ $R_G = 10\text{ }\Omega, V_{GS}=15\text{ V}$	-	12.2	-	ns
Rise time	t_r		-	33.4	-	
Turn-off delay time	$t_{d(off)}$		-	53.6	-	
Fall time	t_f		-	15	-	
Gate charge characteristics						
Gate to source charge	Q_{gs}	$V_{DD}=520\text{ V}, I_D=7\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	5.7	-	nC
Gate to drain charge	Q_{gd}		-	7.2	-	
Gate charge total	Q_g		-	20.7	-	
Gate plateau voltage	$V_{plateau}$		-	5	-	V
Reverse diode characteristics						
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=7\text{ A}$	-	0.85	1.5	V
Reverse recovery time	t_{rr}	$V_R=325\text{ V}, I_F=7\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	373.2	-	ns
Reverse recovery charge	Q_{rr}		-	2.1	-	μC
Peak reverse recovery current	I_{rrm}		-	15.7	-	A

Notes:

- Pulse width limited by maximum junction temperature.
- $L=10\text{mH}, I_{AS} = 8.4\text{A}$, Starting $T_j = 25^\circ\text{C}$.
- $I_{SD} = 7\text{A}, di/dt \leq 100\text{A}/\mu\text{s}, V_{DD} \leq BV_{DS}$, Starting $T_j = 25^\circ\text{C}$.

Electrical Characteristics Diagrams

Figure 1. Typical Output Characteristics

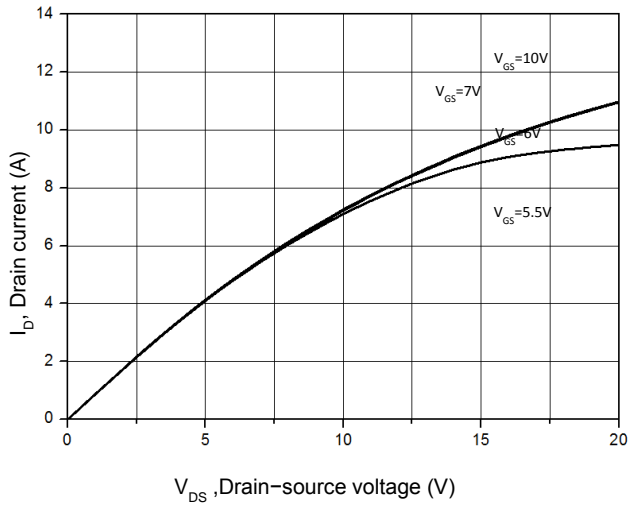


Figure 2. Transfer Characteristics

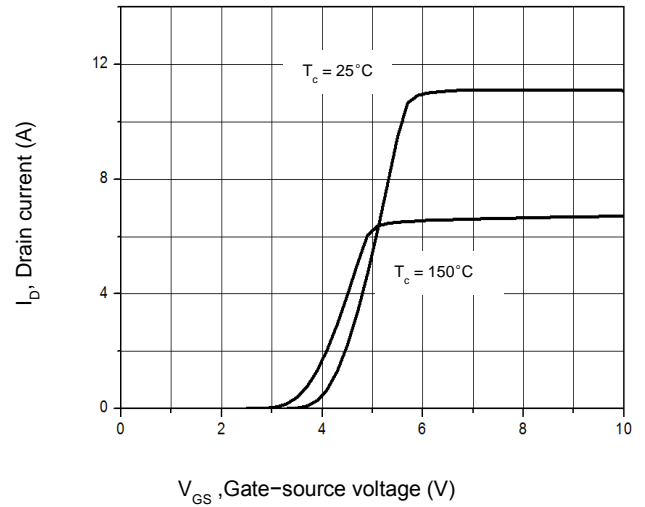


Figure 3. On-Resistance Variation vs. Drain Current

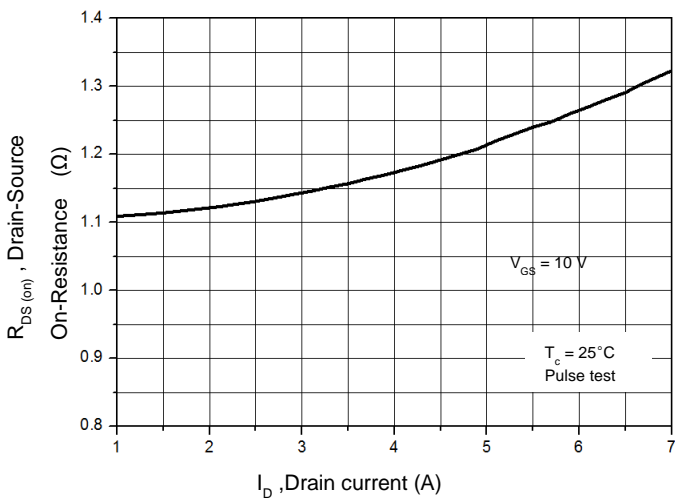


Figure 4. Threshold Voltage vs. Temperature

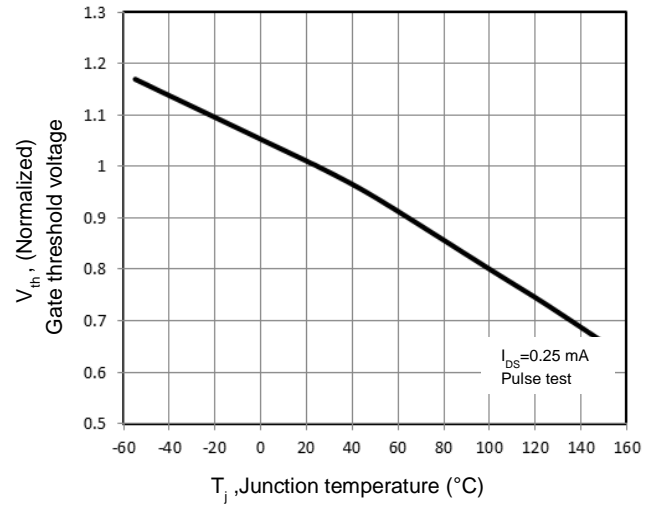


Figure 5. Breakdown Voltage vs. Temperature

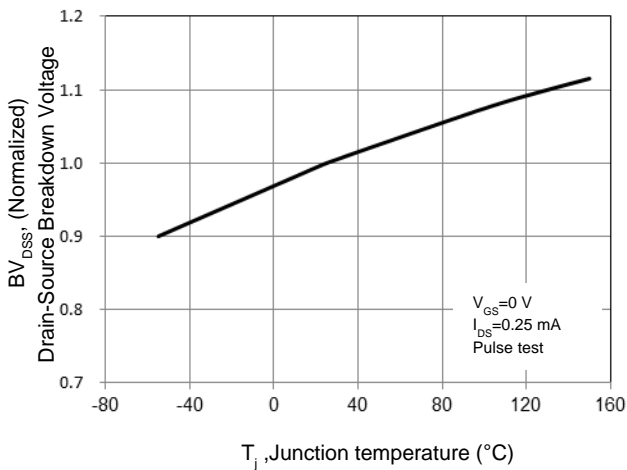


Figure 6. On-Resistance vs. Temperature

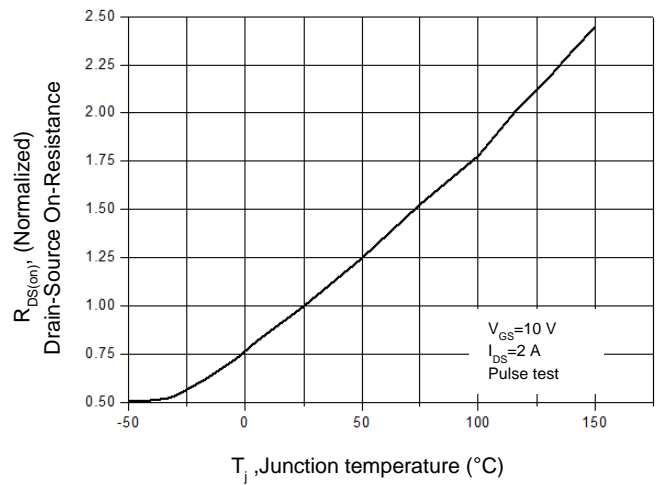


Figure 7. Capacitance Characteristics

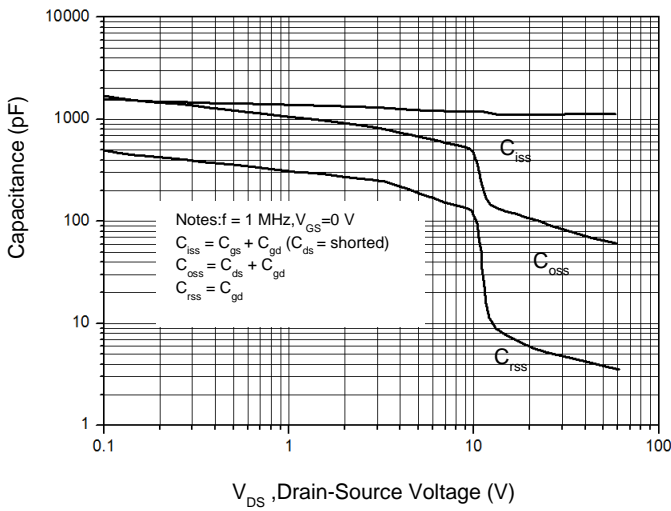


Figure 8. Gate Charge Characterist

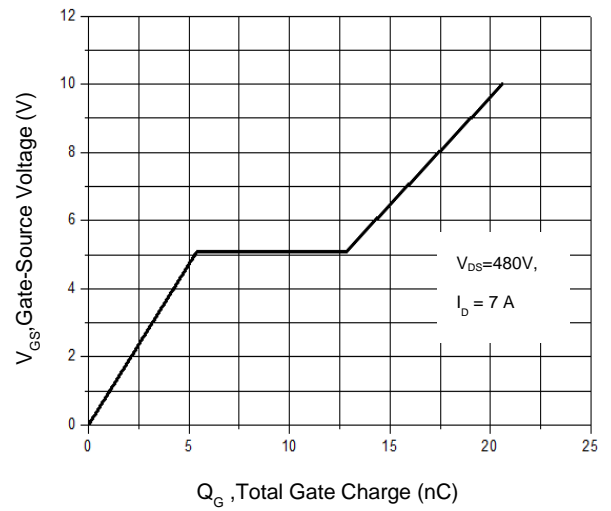


Figure 9. Maximum Safe Operating Area TO-220F

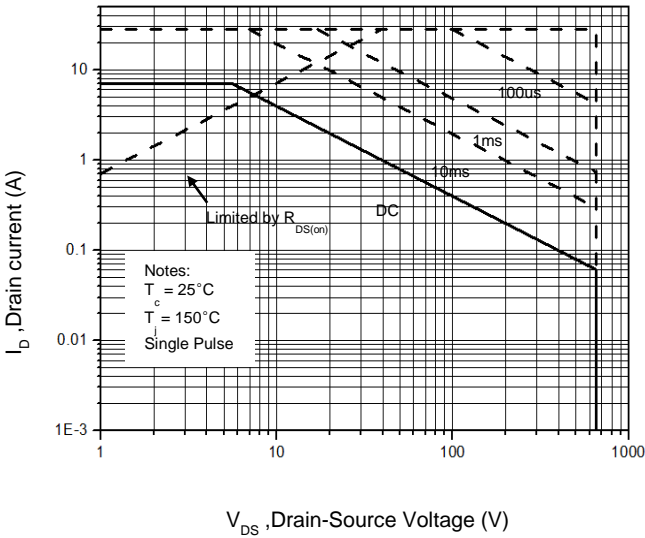


Figure 10. Maximum Safe Operating Area TO-220

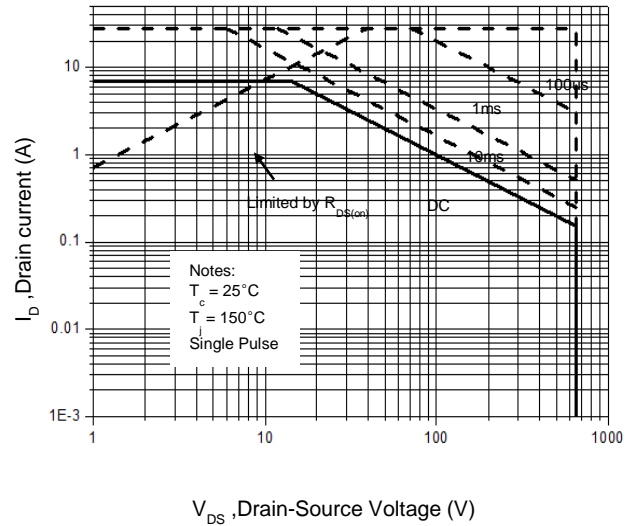


Figure 11. Power Dissipation vs. Temperature TO-220F

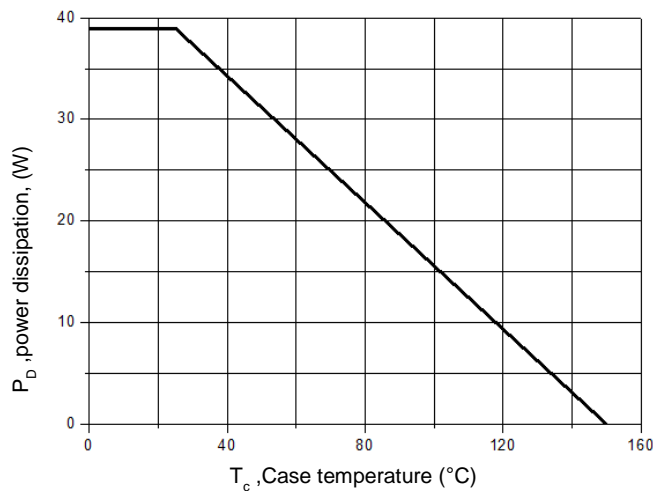


Figure 12. Power Dissipation vs. Temperature TO-220

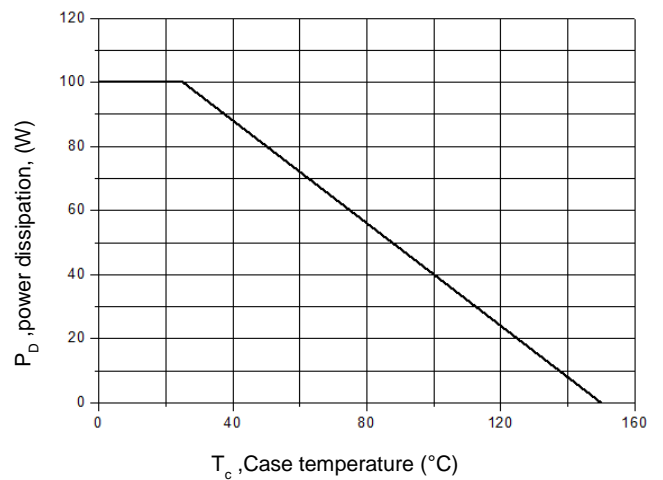


Figure 13. Continuous Drain Current vs. Temperature

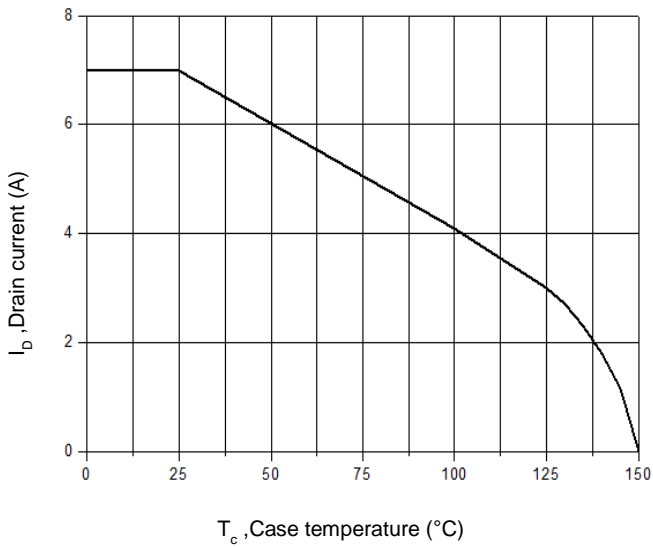


Figure 14. Body Diode Transfer Characteristics

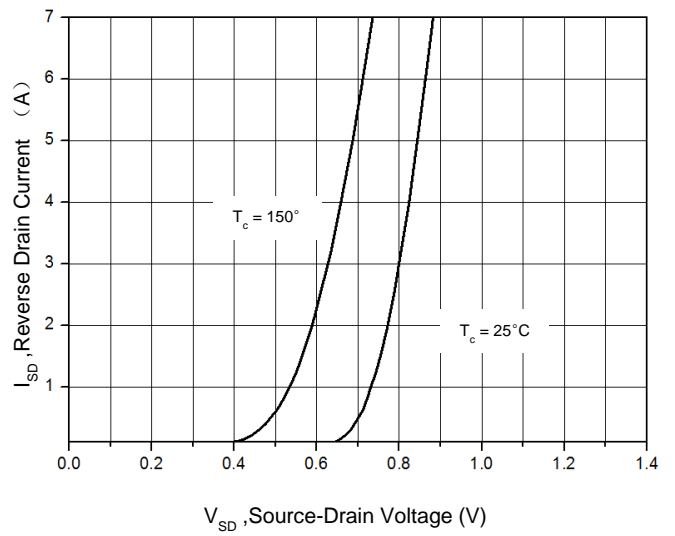


Figure 15 Transient Thermal Impedance, Junction to Case, TO-220F

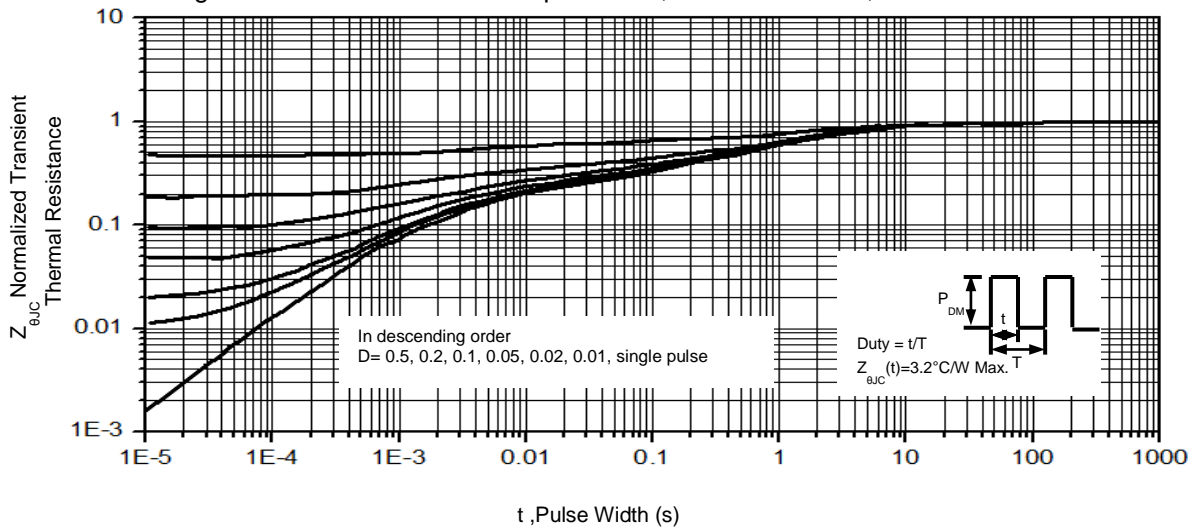
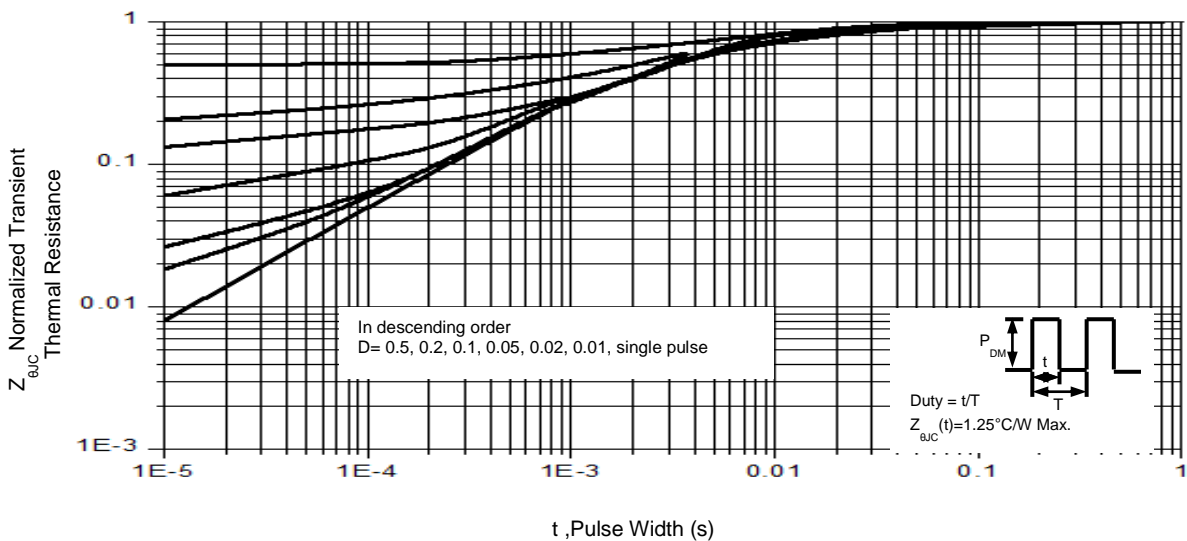
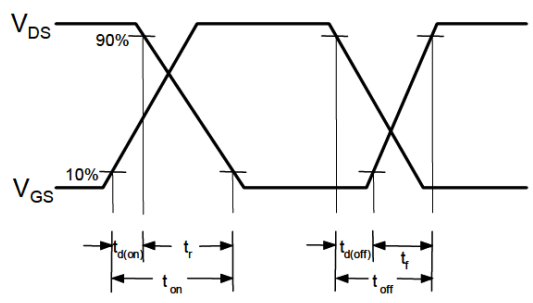
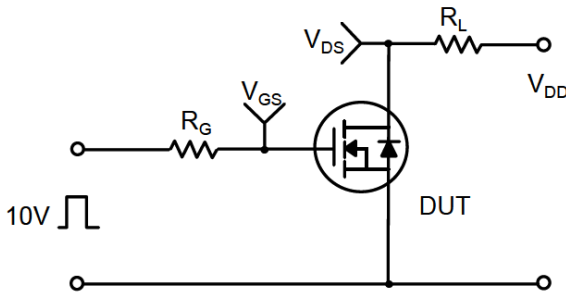
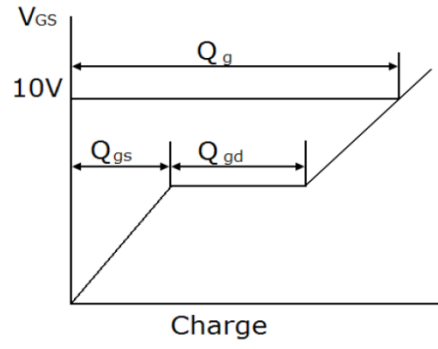
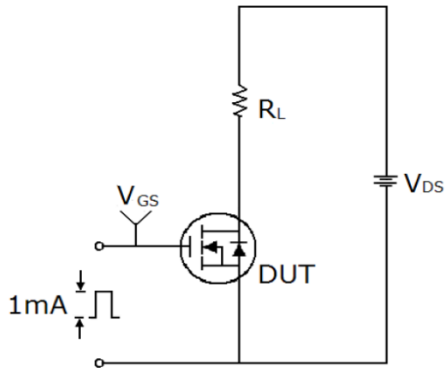


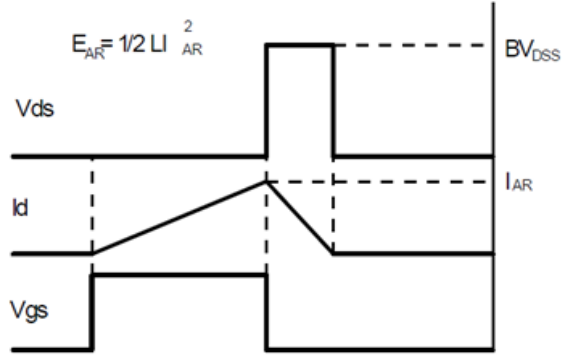
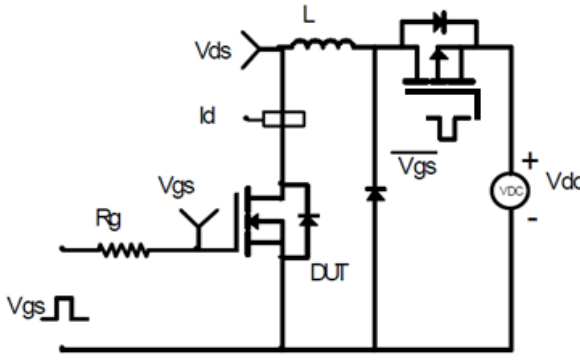
Figure 16. Transient Thermal Impedance, Junction to Case, TO-220



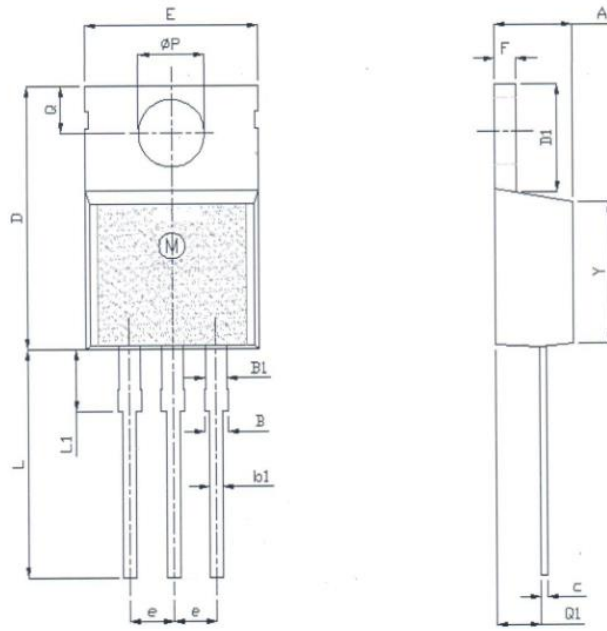
Gate Charge Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveforms



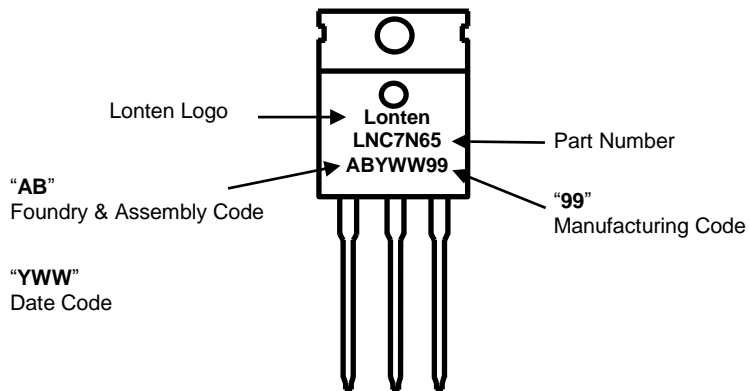
Mechanical Dimensions for TO-220



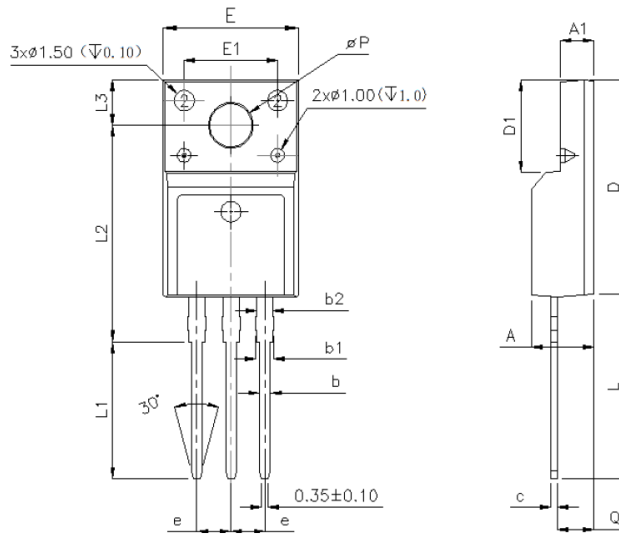
UNIT: mm

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	4		4.8	e	2.44	2.54	2.64
B	1.2		1.4	F	1.1		1.4
B1	1		1.4	L	12.5		14.5
b1	0.75		0.95	L1	3	3.5	4
c	0.4		0.55	ϕP	3.7	3.8	3.9
D	15		16.5	Q	2.5		3
D1	5.9		6.9	Q1	2		2.9
E	9.9		10.7	Y	8.02	8.12	8.22

TO-220 Part Marking Information



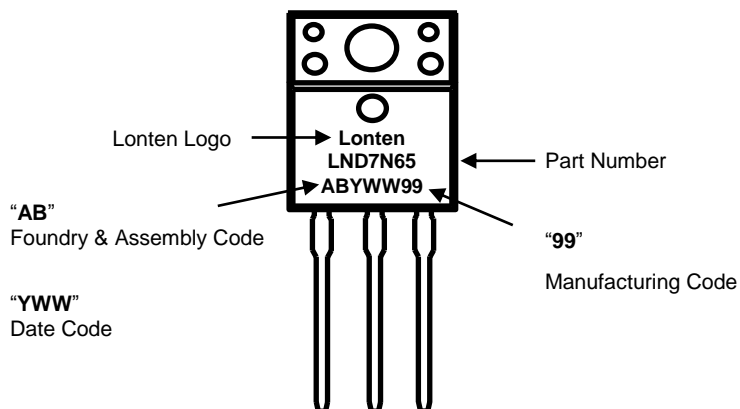
Mechanical Dimensions for TO-220F



UNIT: mm

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	4.5		4.9	E1	6.5	7	7.5
A1	2.3		2.9	e	2.44	2.54	2.64
b	0.65		0.9	L	12.5		14.3
b1	1.1		1.7	L1	9.45		10.05
b2	1.2		1.4	L2	15		16
c	0.35		0.65	L3	3.2		4.4
D	14.5		16.5	ΦP	3		3.3
D1	6.1		6.9	Q	2.5		2.9
E	9.6		10.3				

TO-220F Part Marking Information



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Dec. 2018 Revision 1.1

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